



BROWN

Environmental conditions stress tests on Low Gain Avalanche Diodes

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Hijas Farook^{b,c}, Gabriele Giacomini^b, Spandan Mondal^a, Jennifer Roloff^b,
Enrico Rossi^b, Trevor Russell^a, Alessandro Tricoli^b

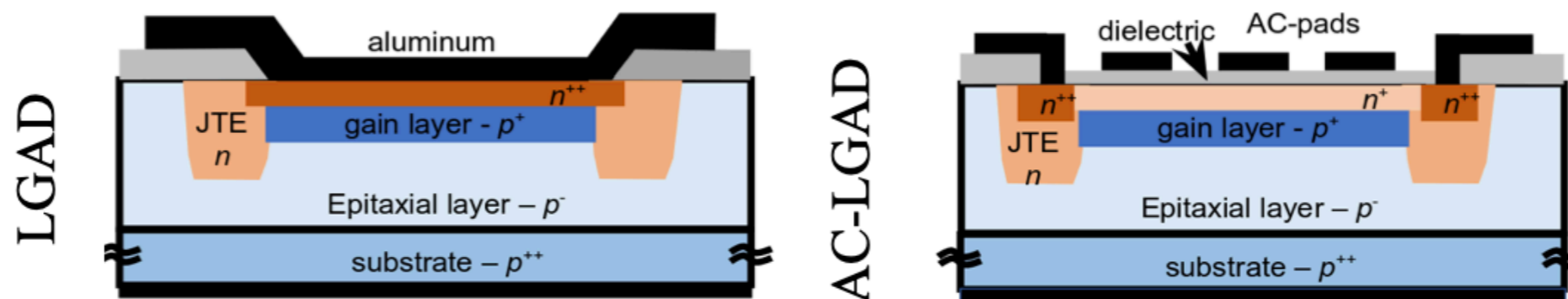
^aBrown University

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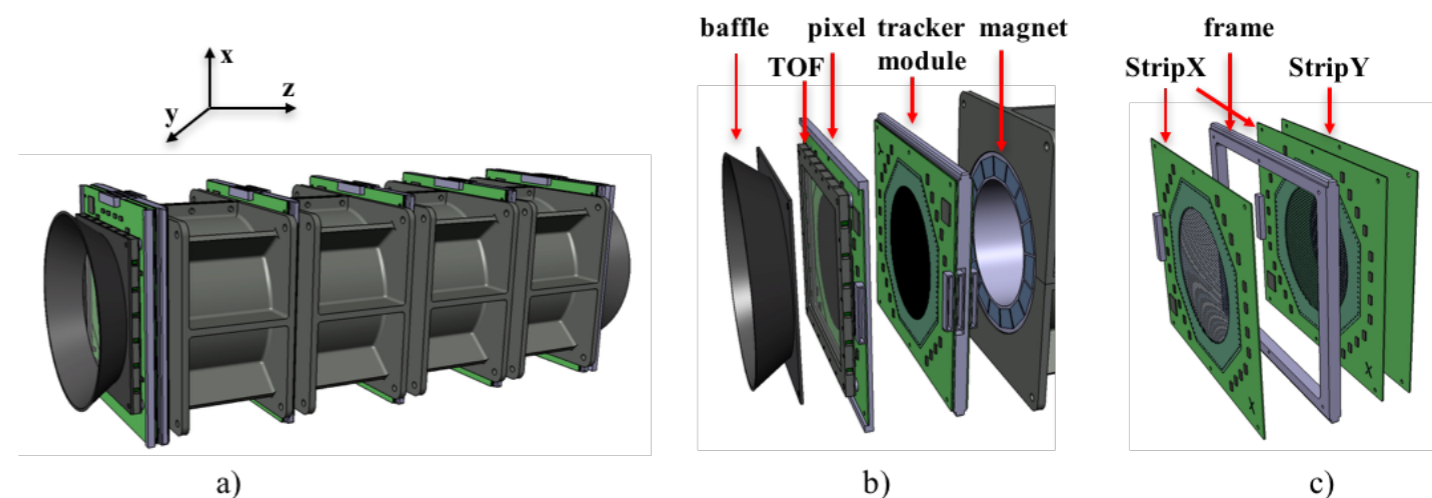
^cUniversity of New Mexico

Introduction

- Low Gain Avalanche Diodes (LGADs) and AC-coupled Low Gain Avalanche Diodes (AC-LGADs):



- ▶ $O(30)$ ps timing performance and 4D extension with $O(10)$ μm spatial resolution in RSD variant
- ▶ Considered for several applications in HEP: Electron-Ion Collider, LHCb Velo Upgrade, ATLAS & CMS High Granularity Timing Detector, Pioneer, ...
- ▶ Application to space-based experiments starting to be investigated [1]
 - ◆ Low power operational needs and their radiation hardness make them suitable devices for providing pico-second-level timing for satellite-based spectroscopy
 - ◆ Ex: time-of-flight detector for Penetrating Particle Analyzer (baseline SiPM) [2]

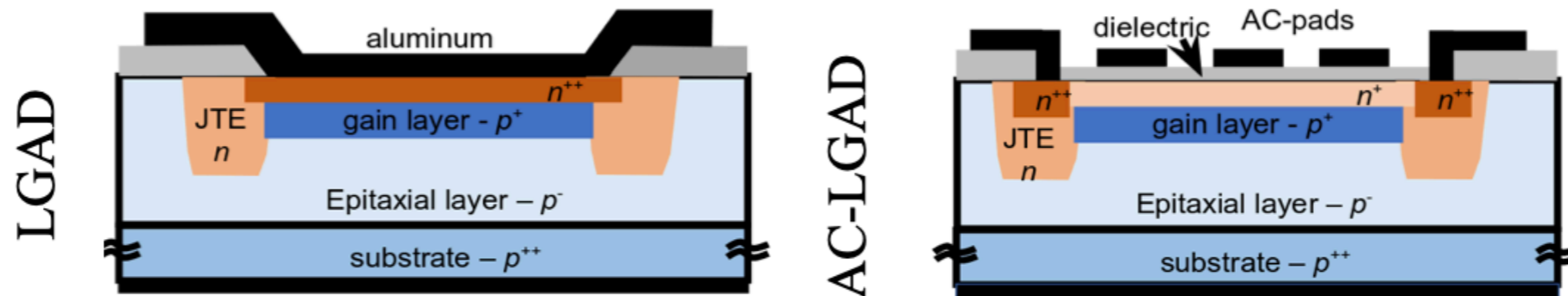


[1] **Characterisation and Stress tests of DC and AC LGAD sensors**, P. Azzarello, G. Barone, D. Boye, W. Chen, G. D'Amen, J. Roloff, G. Giacomini, A. Tricoli, X. Wu, P. Xi, IEEE Nuclear Science Symposium and Medical Imaging Conference (2022).

[2] **Penetrating Particle ANalyzer (PAN)** X.Wu et al., Adv. Space Res. 63, 8, 2672-2682 (2019) <https://doi.org/10.1016/j.asr.2019.01.012>

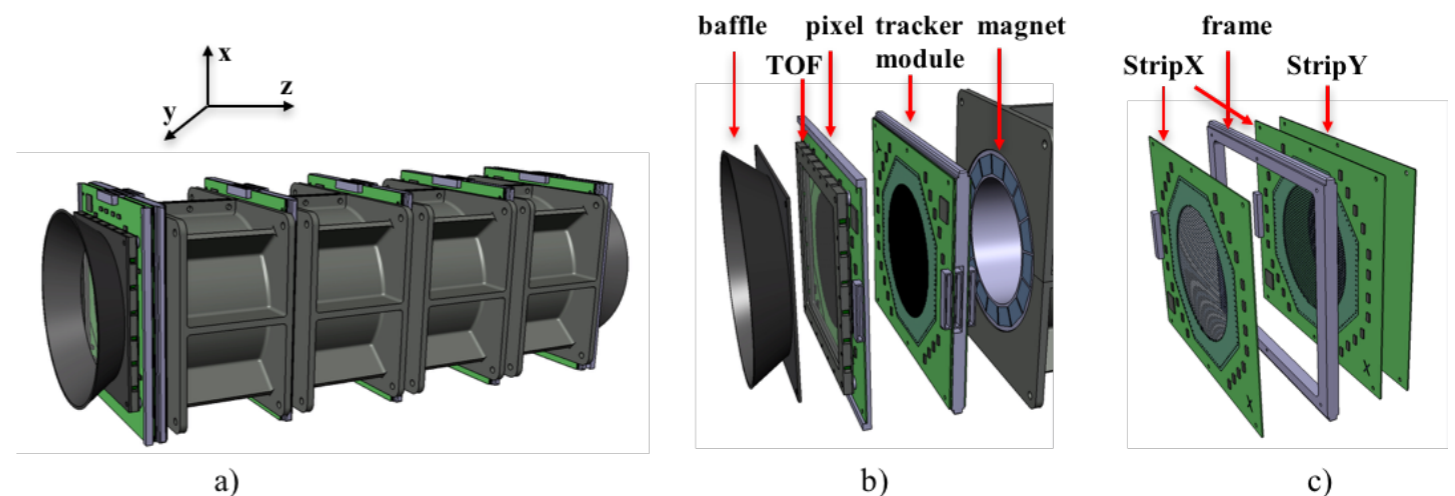
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- ▶ Application to space-based experiments starting to be investigated [1]
- ▶ Sensor fabrication can be specifically targeted
 - ◆ Tuning the sensor's size, the gain characteristics, and the depletion layers size.
- ▶ Application-specific design can be targeted: specific needs are reached in terms of material budget, energy consumption, and climate-change resilience.

[1] **Characterisation and Stress tests of DC and AC LGAD sensors**, P. Azzarello, G. Barone, D. Boye, W. Chen, G. D'Amén, J. Roloff, G. Giacomini, A. Tricoli, X. Wu, P. Xi, IEEE Nuclear Science Symposium and Medical Imaging Conference (2022).



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Environmental conditions

- A large set of studies actively performed on LGADs & AC-LGADs

- ▶ In cryogenic and laboratory-controlled conditions.

- Space applications require the study of LGAD behavior in a wide range of environmental conditions.

- ▶ Temperature variations -100°C and $+100^{\circ}\text{C}$

- ▶ Payload limitations: temperature control not ensured

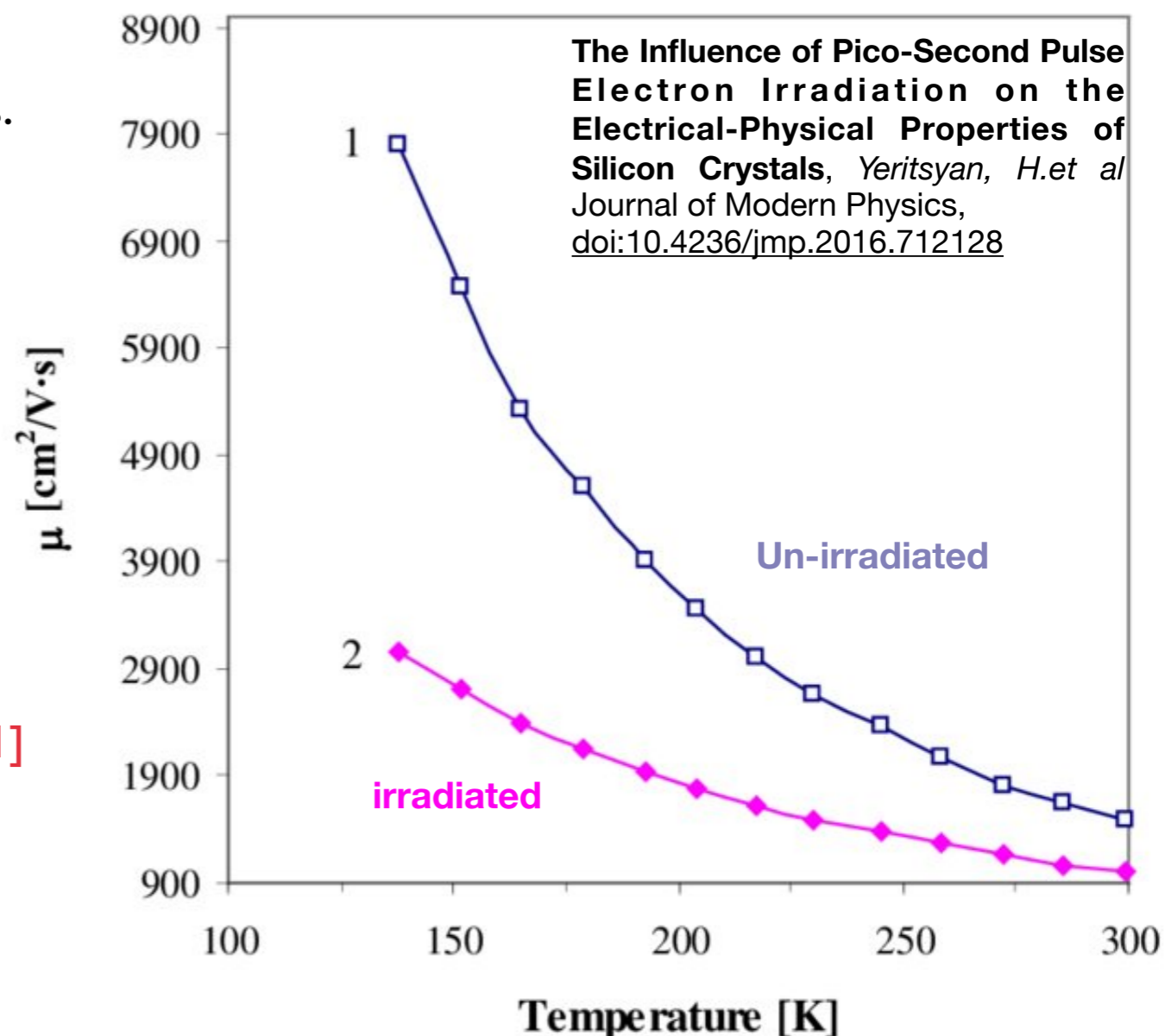
- Charge carrier mobility:

- ▶ Decreases as temperature increases due to phonon scattering.

- ▶ The mobilities decrease as the doping concentration increases due to the scattering from the dopants.

➔ Gain reduction as a function of temperature increase [1]

- Need to ensure good sensor response and electrical characteristics at varying operating conditions.



Silicon crystal (n-Si) charge carrier's mobility temperature dependence after electron pico-second beam irradiation (3.5 MeV).

[1] Gain suppression mechanism observed in Low Gain Avalanche Detectors, Esteban Currás, Marcos Fernández, Michael Moll [arXiv:2107.10022](https://arxiv.org/abs/2107.10022)

Sensors & setup

- BNL-produced sensors [1] with uniform p-type implants on the silicon surface.

- ▶ 1.3 mm² with gain layers doses of $2.8 \times 10^{12} \text{ cm}^{-2}$ (50 μm) and $2.25 \times 10^{12} \text{ cm}^{-2}$ (20 μm), respectively, were tested.
- ▶ With and without a passivation layer.
- ▶ For the AC-LGAD sensors: strips with both fixed pitch and variable pitch for an active area of 0.5 cm \times 0.5 cm from 50 μm thick devices.

- Probe-station setups used in reverse bias:

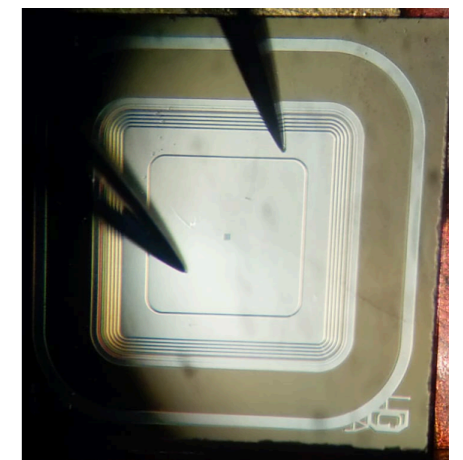
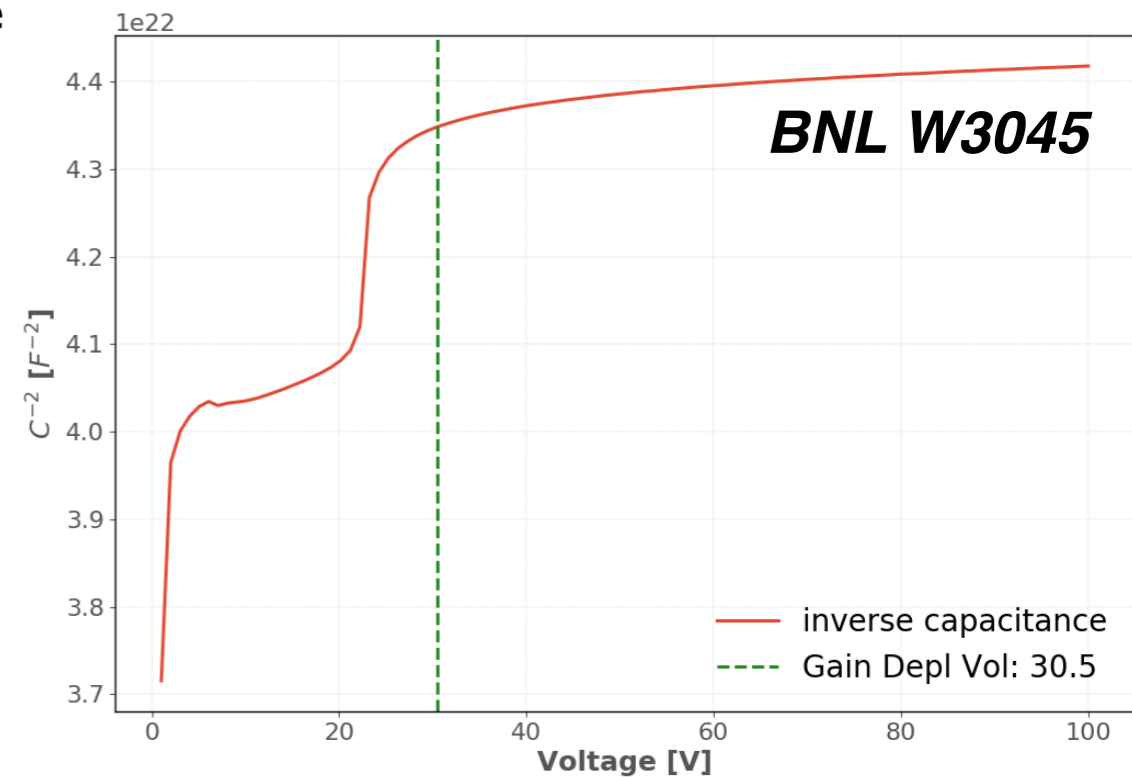
- ▶ Brookhaven climate chamber with two-needle probe-station readout (compliance at 10^{-6} A/V).
- ▶ RD50's (CERN) characterization laboratory, with a two-needle probe station setup (compliance at 10^{-6} A/V).

- Thermal & humidity control:

- ▶ RD50: ethanol chiller for cooling and heating in the ranges of $T = -30^\circ\text{C}$ to $T = +30^\circ\text{C}$, dry air for humidity control $\sim 20\text{-}30\%$
- ▶ BNL: ambient chamber $T = -60^\circ\text{C}$ to $T = +180^\circ\text{C}$ with varying humidity.
- ▶ N_2 is supplied to vary relative humidity and to prevent condensation when operating at cryogenic temperatures

- Thermalization and wait time:

- ▶ Thermal imaging camera to ensure thermalization is reached.



[1] Development of a technology for the fabrication of Low-Gain Avalanche Diodes at BNL G. Giacomini, W. Chen, F. Lanni and A. Tricoli, Nucl. Instrum. And Meth. In Phys. Res. <https://doi.org/10.1016/j.nima.2019.04.073>.

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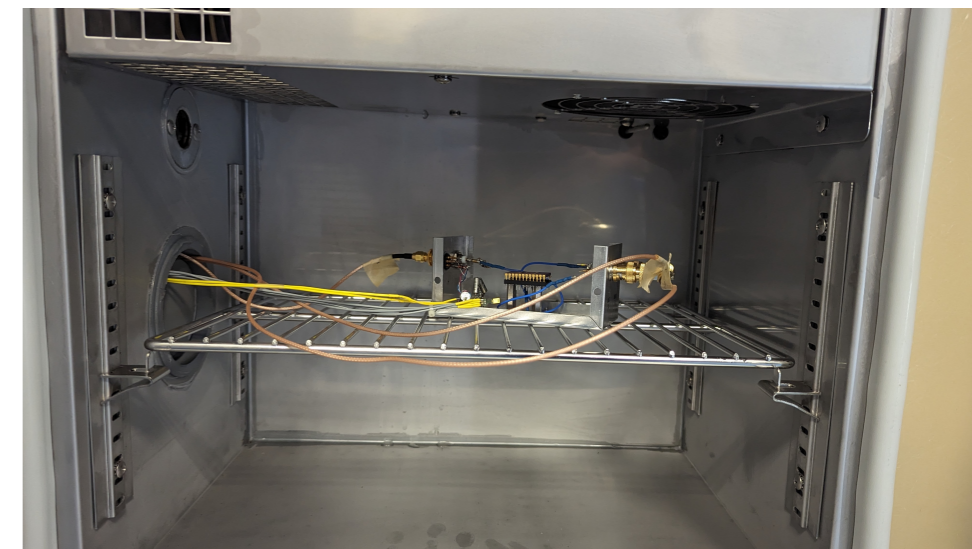
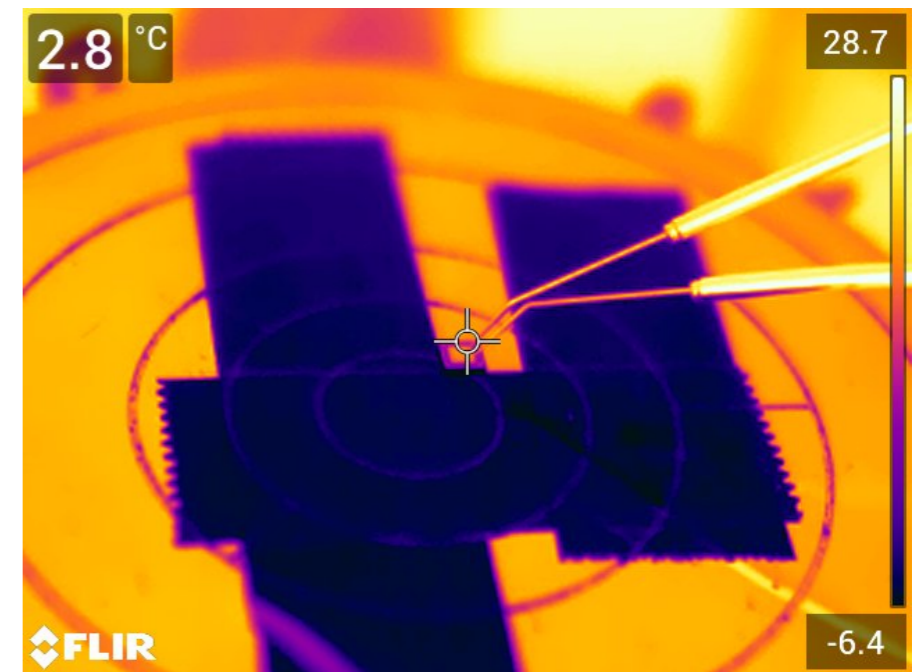
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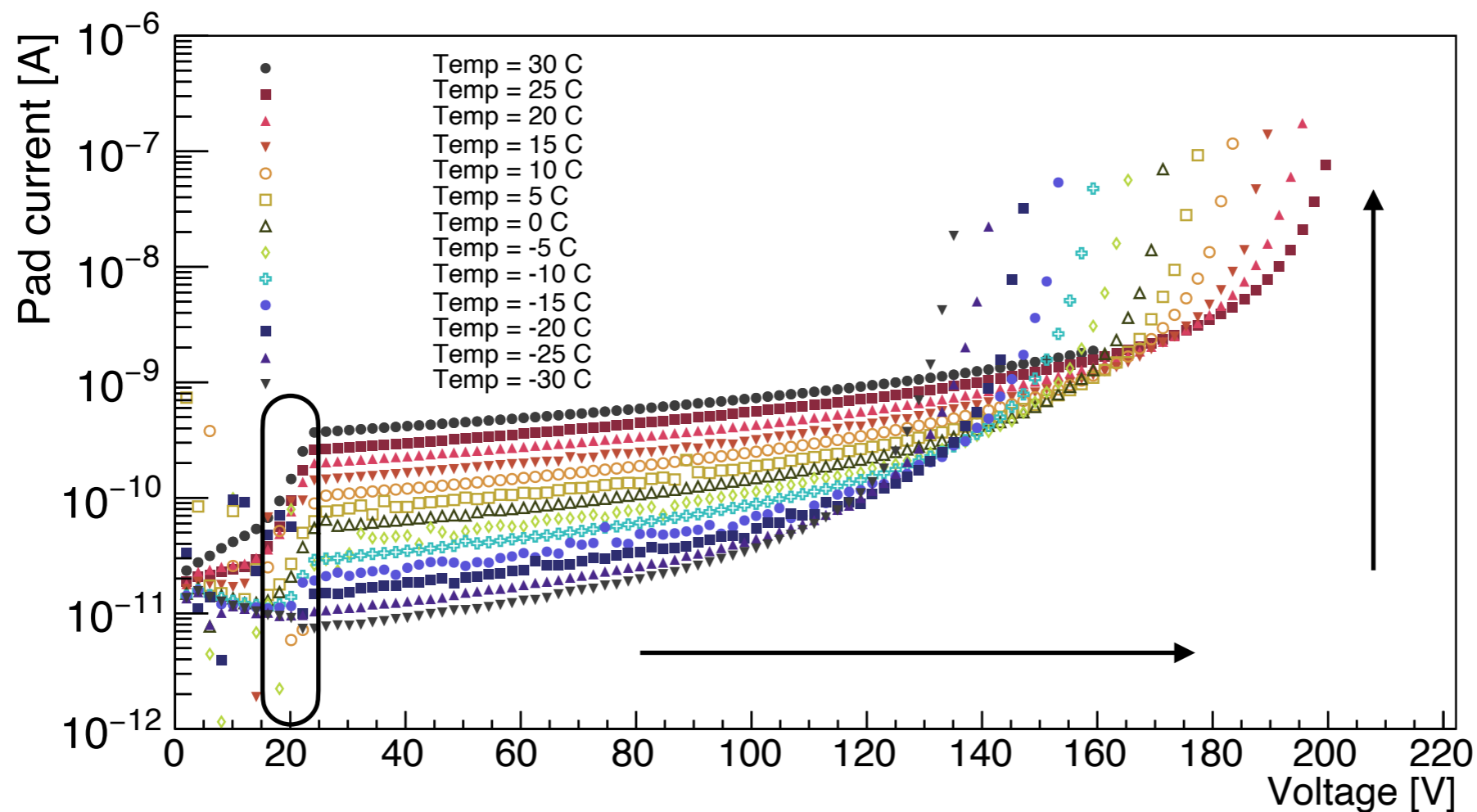
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Thermal profile

- Measurement segmentation in sweeps
 - ▶ To stress test the sensors four sequential temperature scans are performed in intervals of 5°C and a period of 60°C.
 - ▶ After reaching a temperature of $T = +30^{\circ}\text{C}$ all the $I(V)$ measurements are repeated by now decreasing the temperature by steps 5 °C.
 - ▶ Use each set of two measurements as a self-cross-check with respect to changing conditions (humidity)
 - ▶ Further stress tests are performed by abruptly changing the temperature changes between the cold and warm regimes.
- Depletion voltage is independent of the temperature, but leakage current and break-down are.



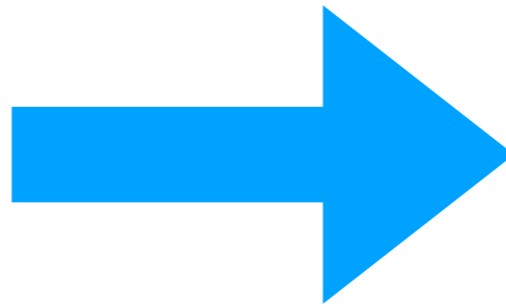
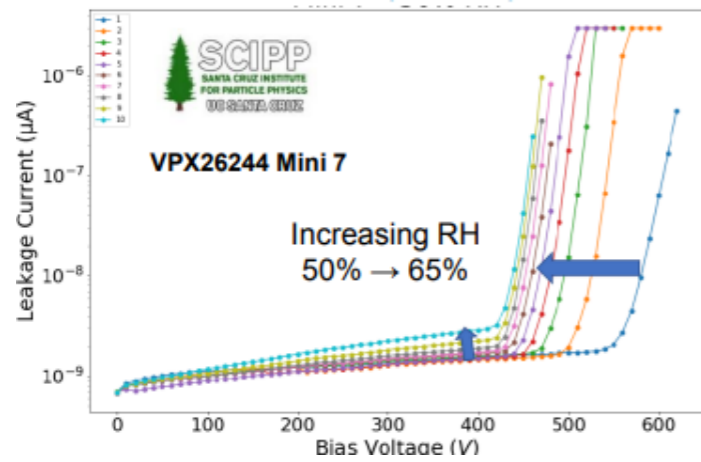
Leakage current increase with T

Breakdown voltage increase with T

Environmental changes

- Segmentation of temperature sweeps as a function causes that can impact the performance.

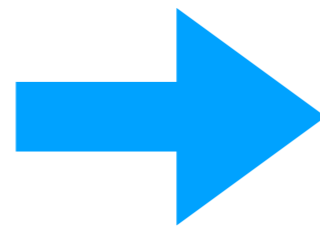
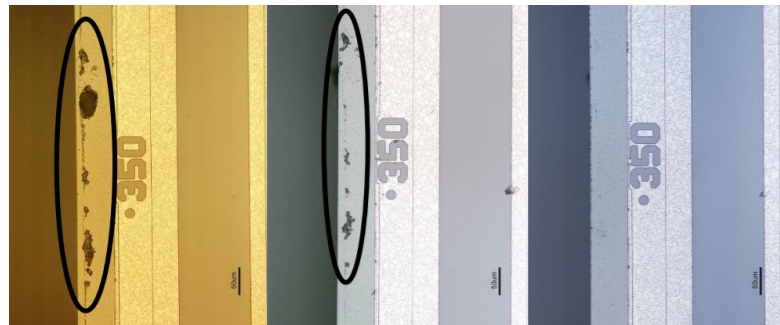
- ▶ Humidity can reduce dielectric strength, influence from guard ring metals [1]



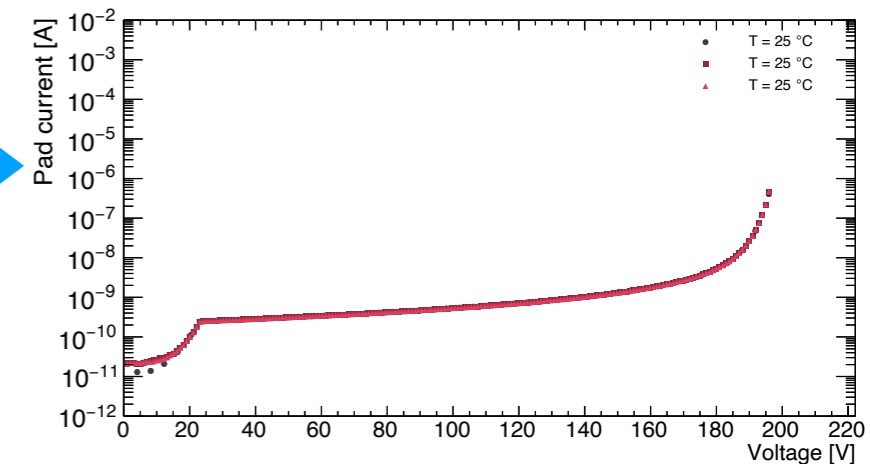
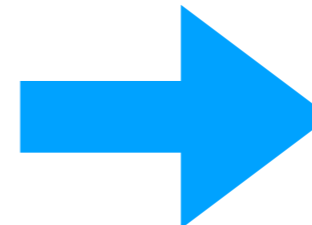
Humidity-controlled environments with dry-air desiccators



- ▶ Static charge accumulation [2], ex: storage medium, handling



de-ioniser



- ▶ Implant-related temperature dependence [3]

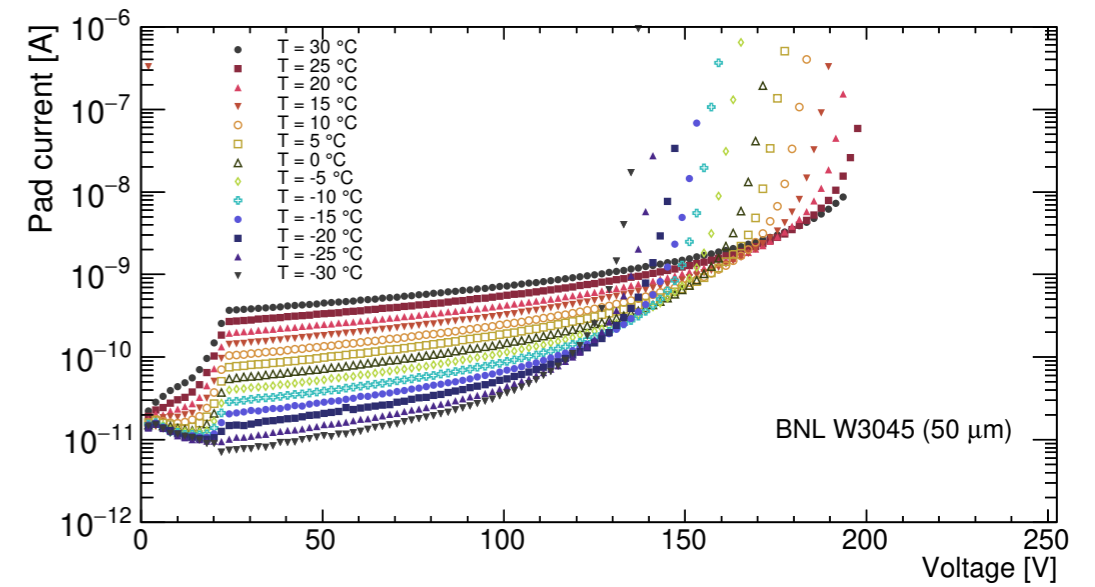
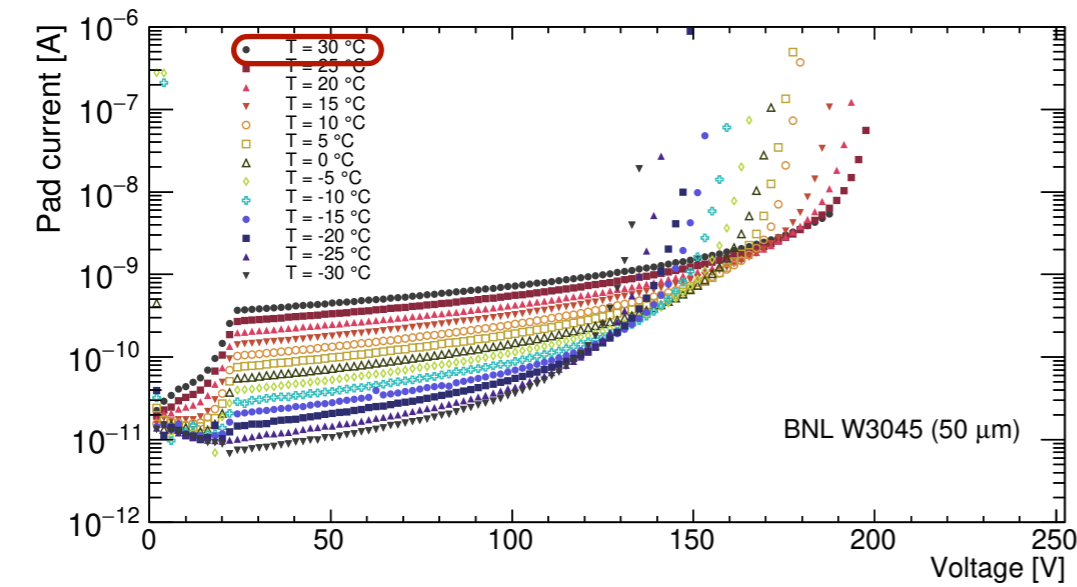
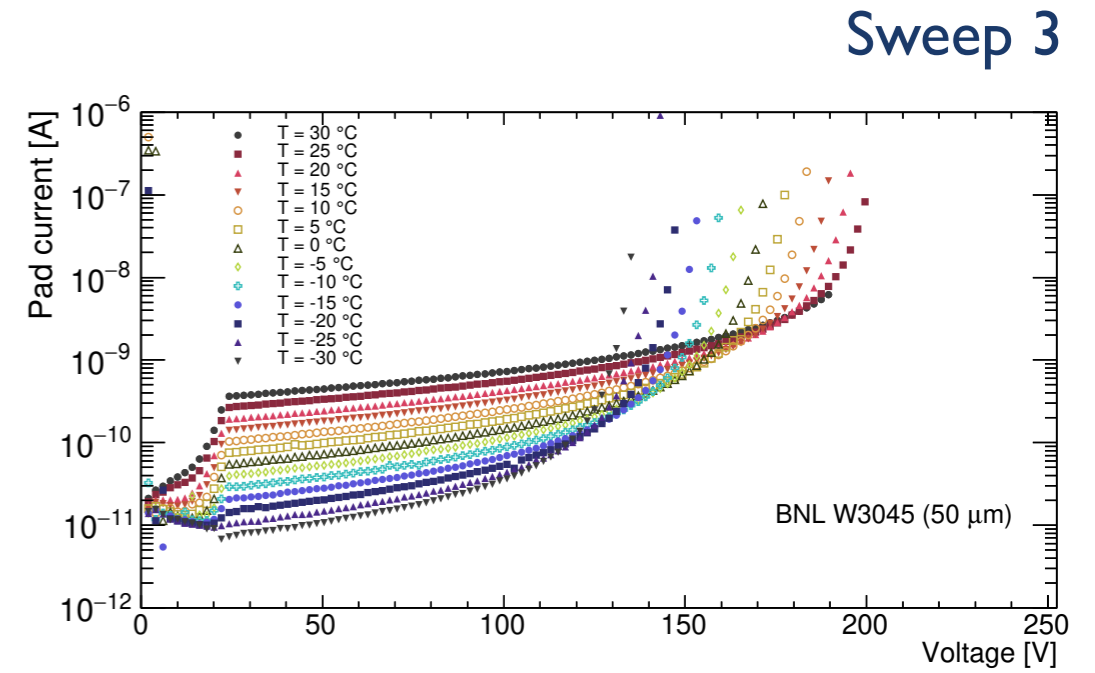
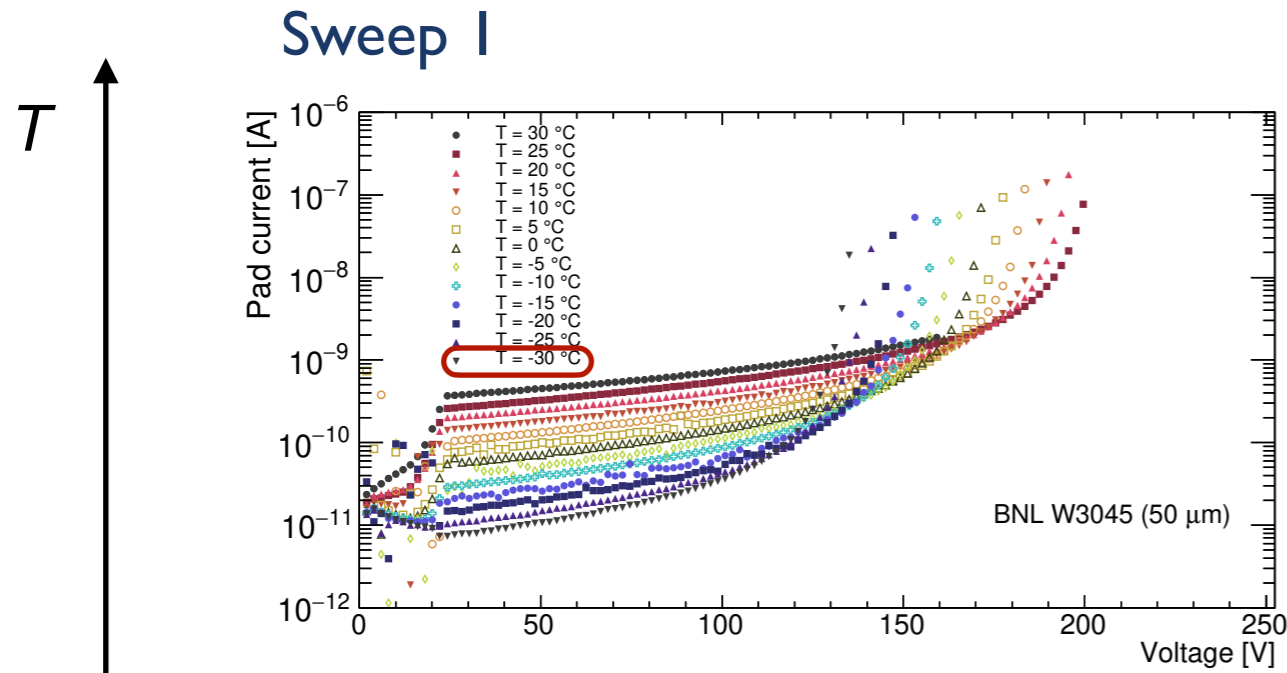
[1] Humidity Sensitivity of Large Area Silicon Sensors: Study and Mitigation, X. Fernández-Tejero et al, HSTD12, Hiroshima 2019

[2] Strip sensor performance in prototype modules built for ATLAS ITk, C. Helling et al, <https://doi.org/10.1016/j.nima.2020.164402>

[3] Study of impact ionization coefficients in silicon with Low Gain Avalanche Diodes, E. Rivera and Michael Moll, <https://arxiv.org/pdf/2211.16543.pdf>

Thermal profile

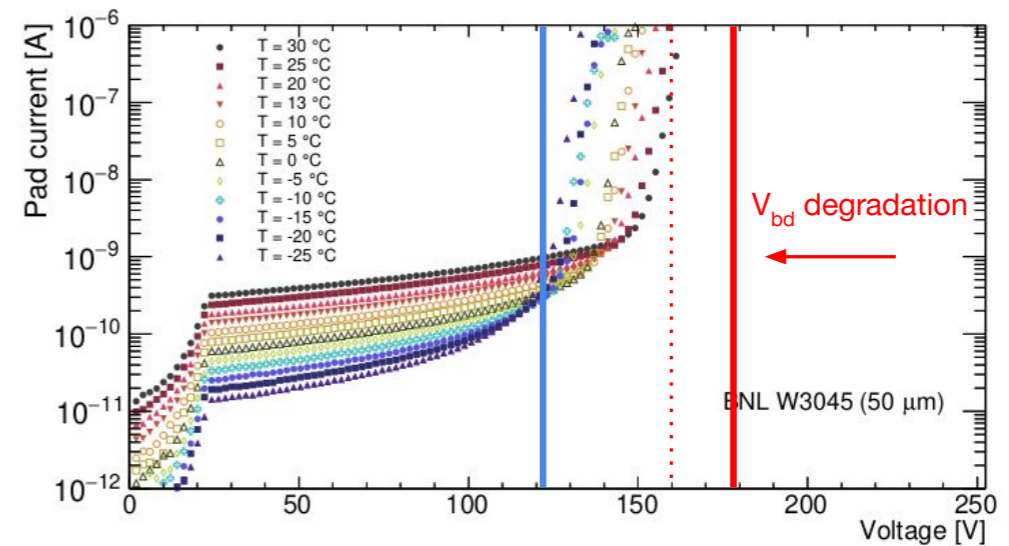
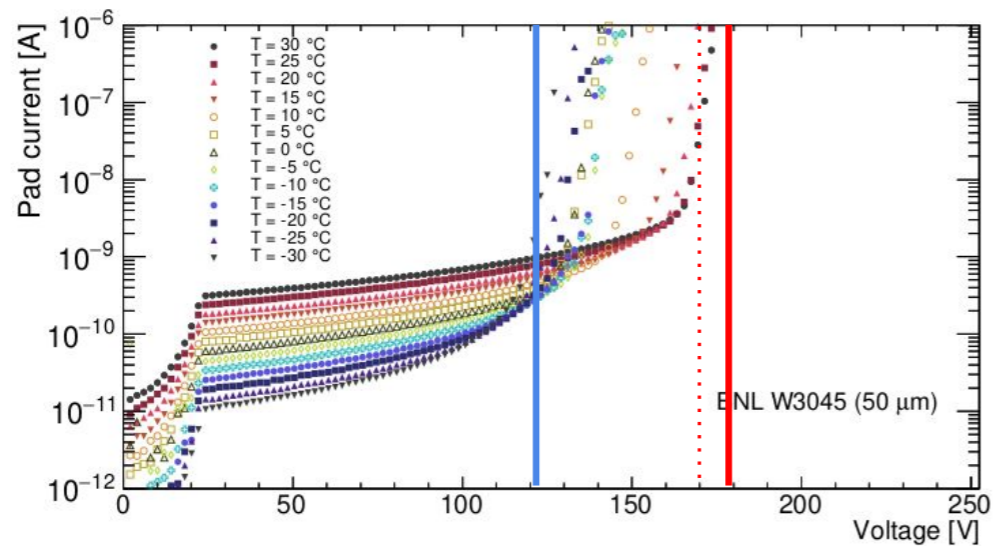
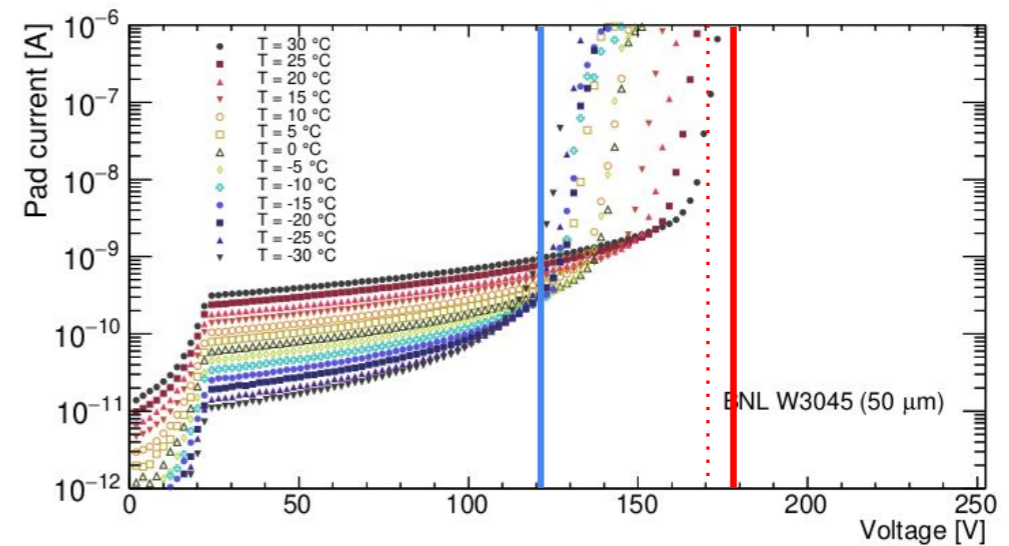
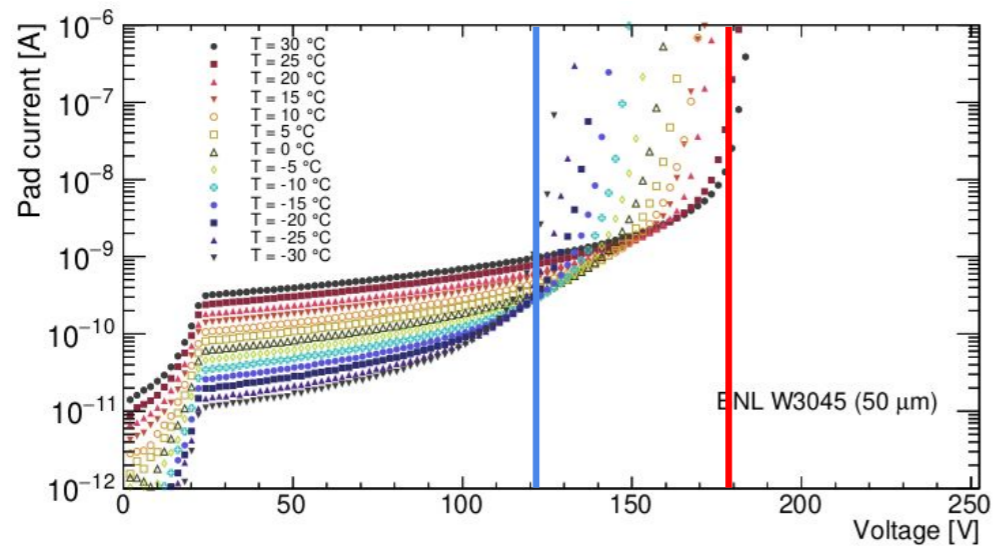
- Studies repeated for stability under rapidly changing conditions.
 - ▶ by abruptly changing the temperature changes between the cold (-30°C) and warm regimes ($+30^{\circ}\text{C}$)



T ↑

Thermal profile

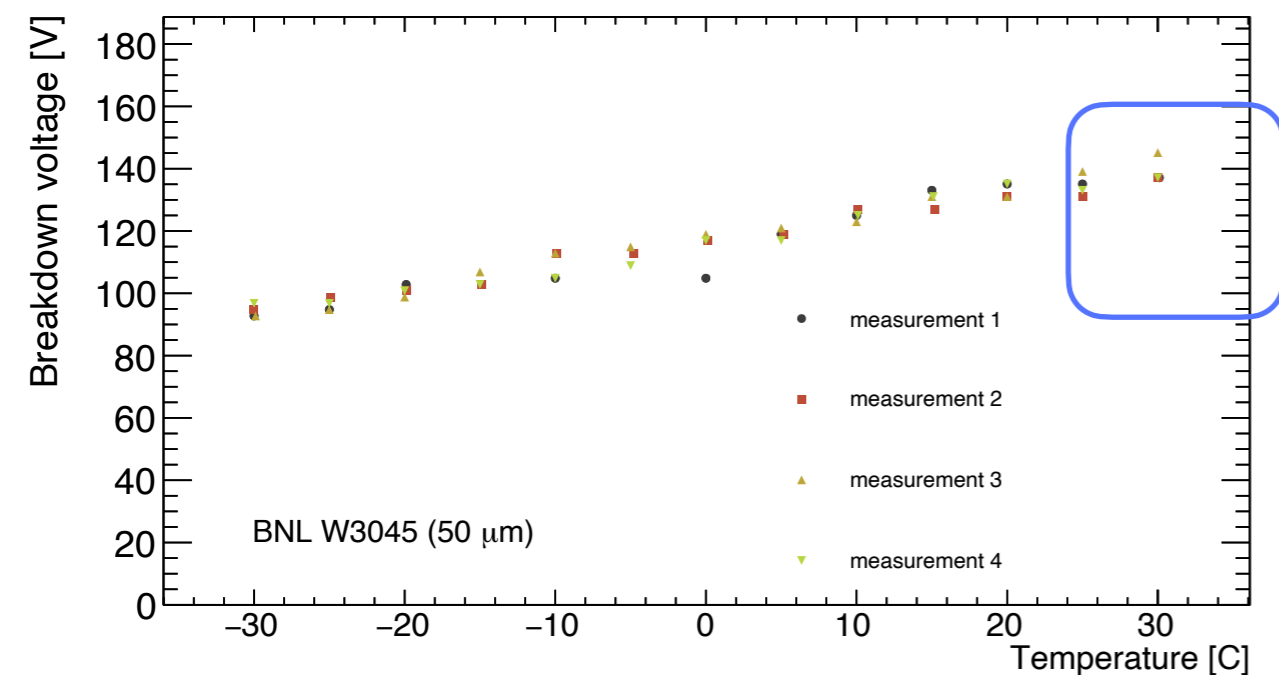
- Testing in extreme scenarios: unpassivated sensors with the pad exposing bare metal.
 - ▶ Observing permanent performance degradations of LGAD breakdown biases.
 - ▶ De-ionization tests seem to point at a static charge accumulation or humidity-related impacts.



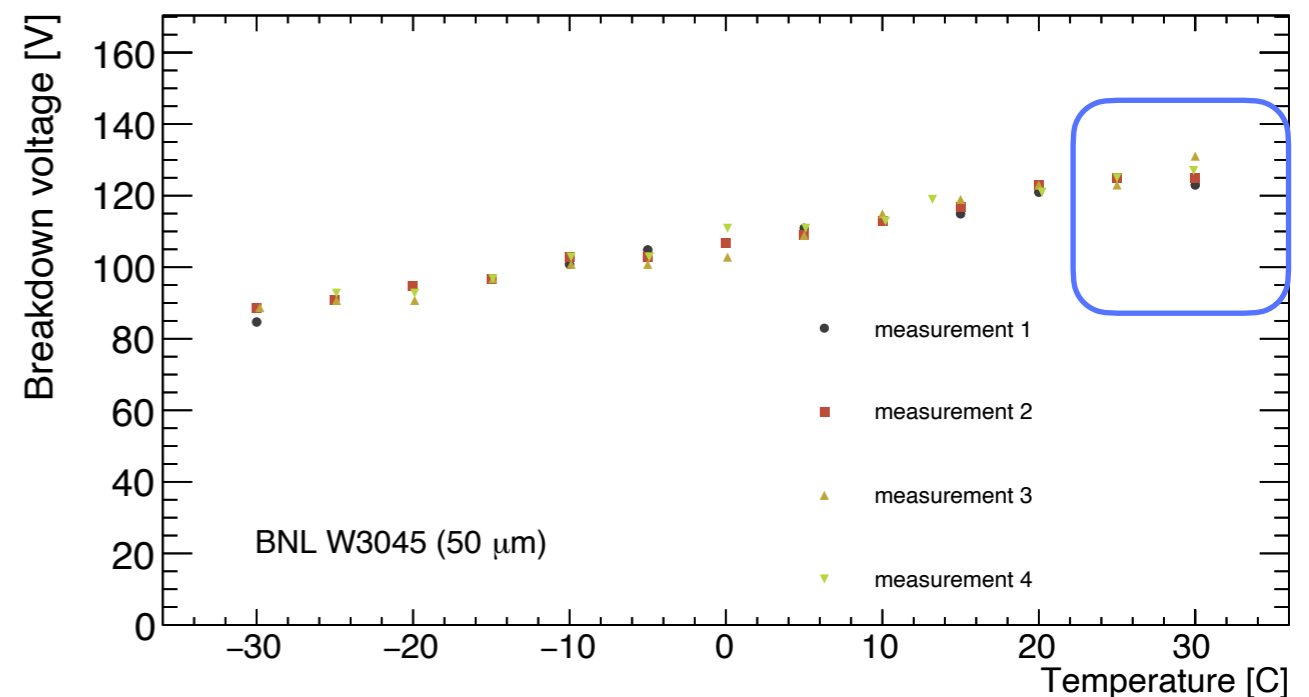
Thermal profile

- Studies repeated for stability under rapidly changing conditions.
 - ▶ Breakdown voltage extracted from two exponential fits with χ^2 as a discriminator.
 - ▶ Within a given thermal cycle we do observe the linear profile evolution of a diode.
 - ▶ These results show that the electrical characteristics of the BNL-produced sensors retain good operating performance at a wide range of temperatures.
 - ▶ Further tests with short thermalization times or abrupt temperature variations from $T = -30^\circ\text{C}$ to $T = +30^\circ\text{C}$ without relaxation times show a similar resilience.
 - ▶ The linear model loses validity at high temperatures where thermal effects might induce early breakdowns.

Sweep 1+2

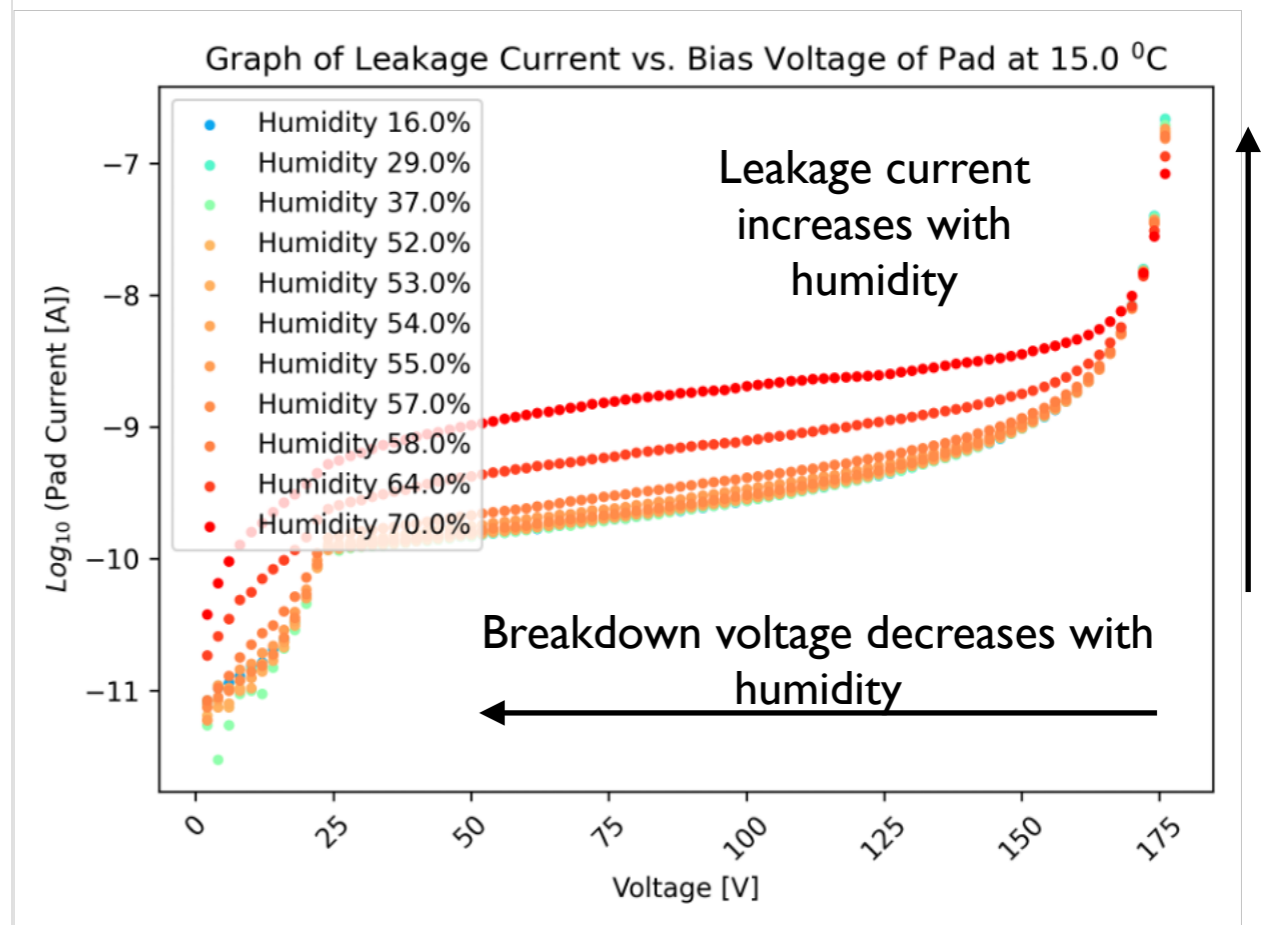
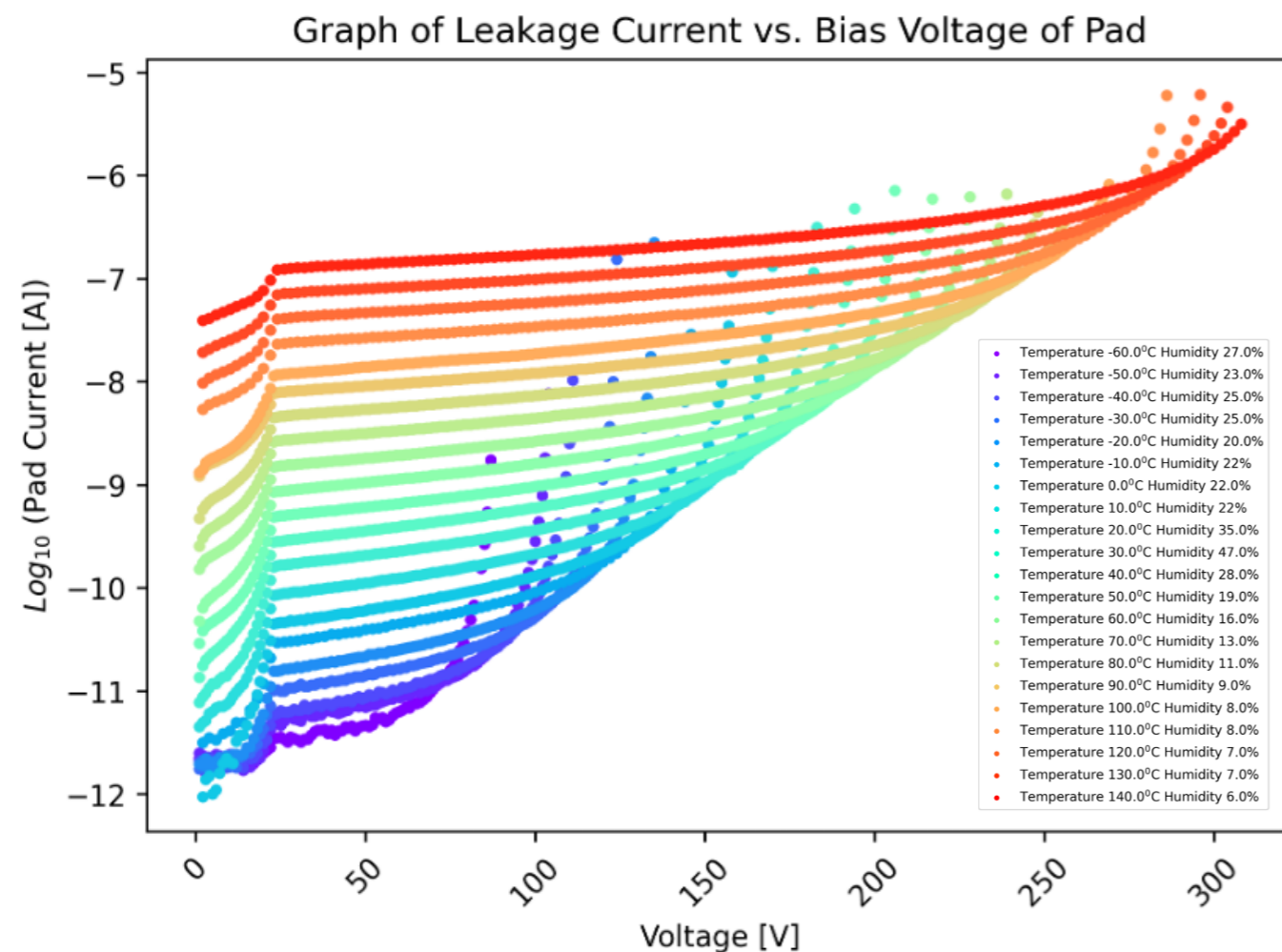


Sweep 3+4



Humidity investigations

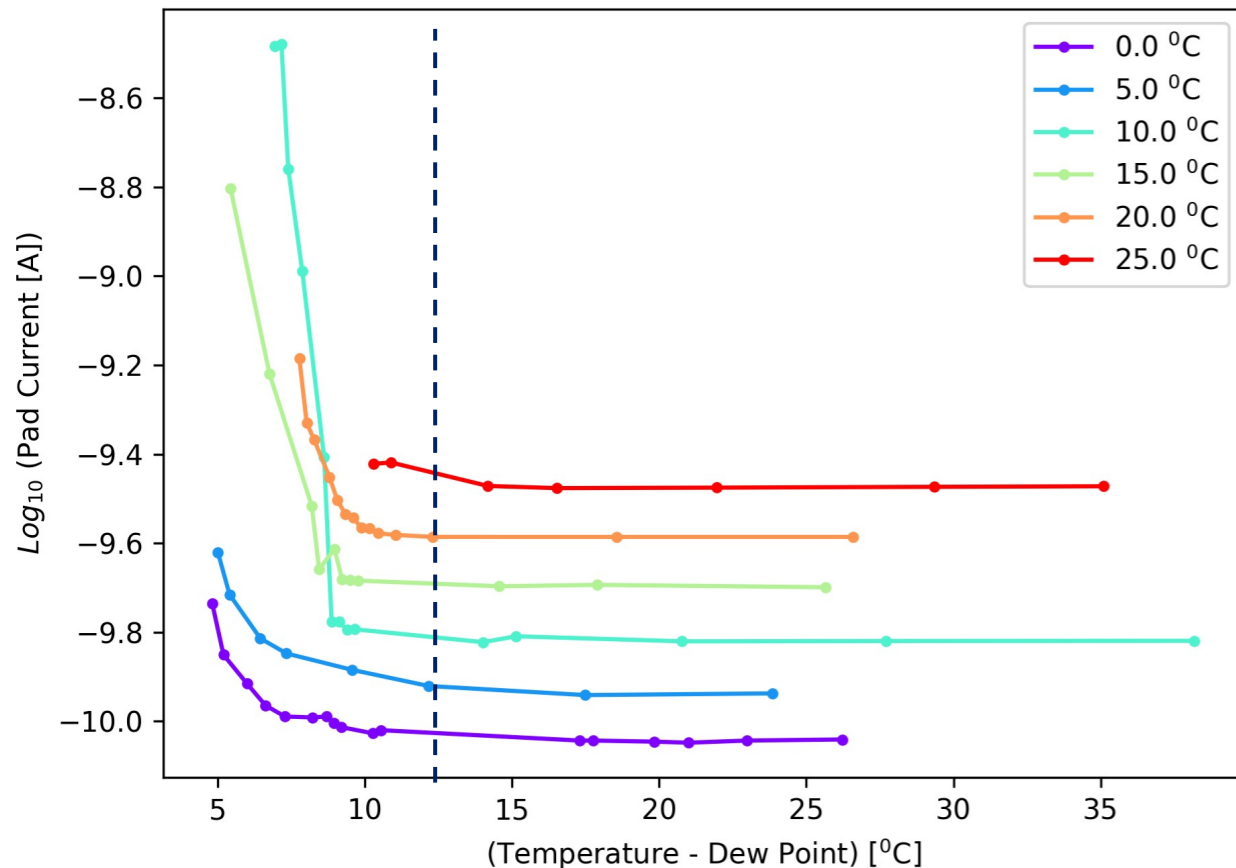
- $I(V)$ measurements are taken at temperatures from -60°C to 140°C with varying humidities.
 - ▶ Reaching higher temperatures is difficult with the cabling used.
 - ▶ Measurements repeated from low humidity to high and reversely.
 - ▶ Difficult to create higher humidity conditions with higher temperatures in the climate chamber.
- As expected leakage current and breakdown voltage increase with temperature, independently of the humidity.
 - ▶ At fixed temperatures, pad current remains the same until a *critical humidity*.
 - ▶ Leakage current increases when the dew point is around $\sim 10^{\circ}\text{C}$ less than the sensor temperature



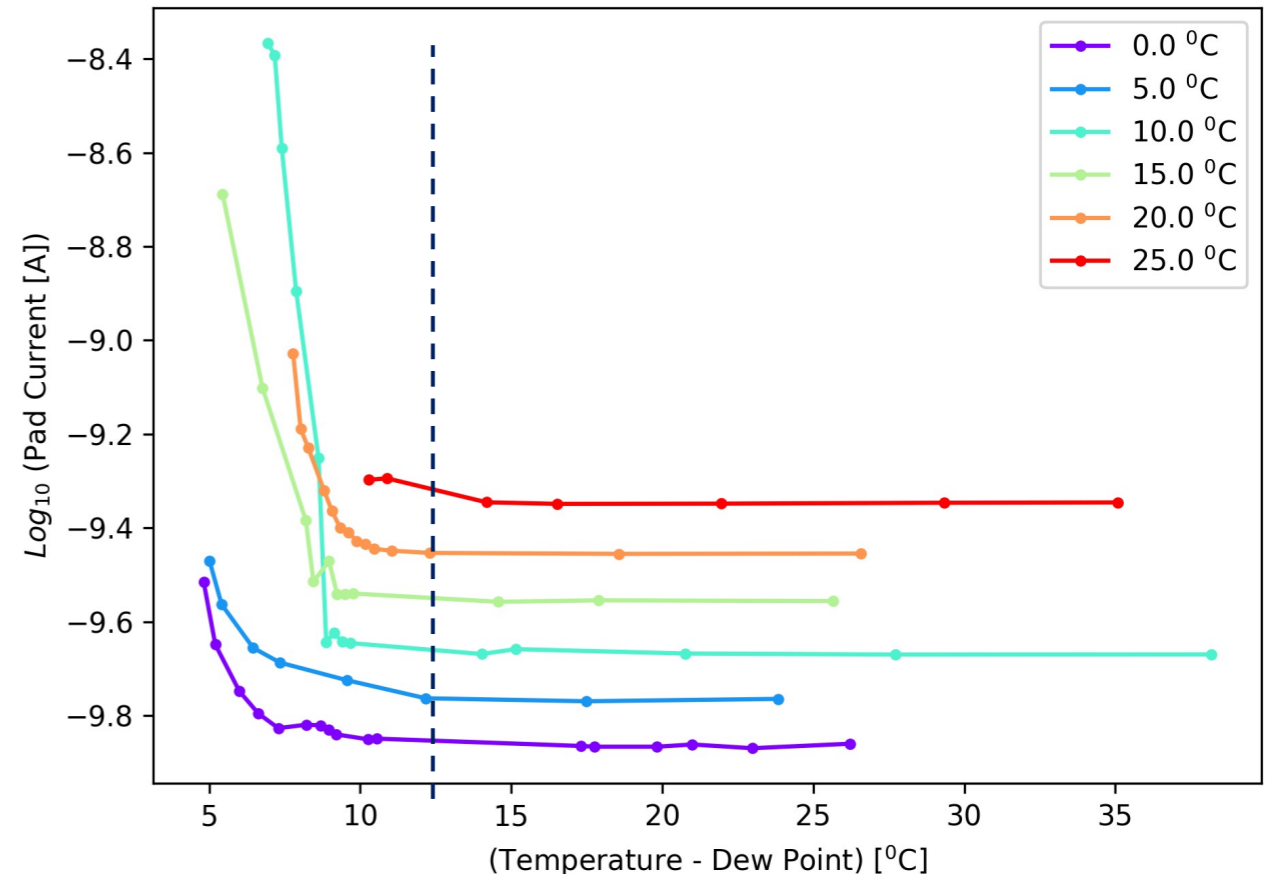
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- Performance degradation with humidity:
 - ▶ Transient performance degradation.
 - ▶ Reversible, as cyclical tests were performed.

Leakage Current vs. Relative Humidity at 76.0 V

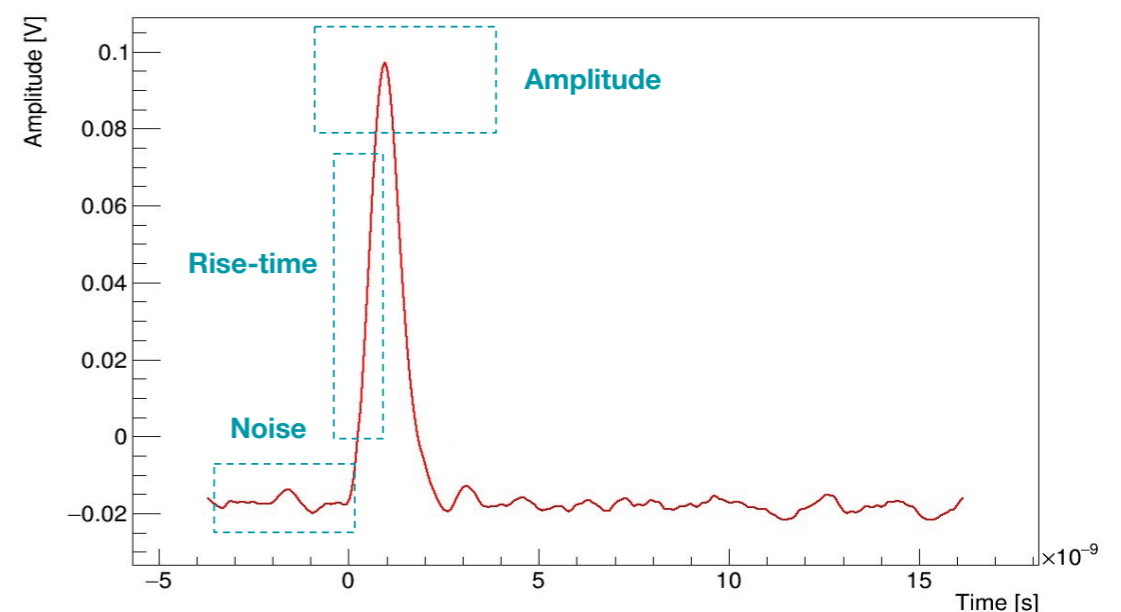
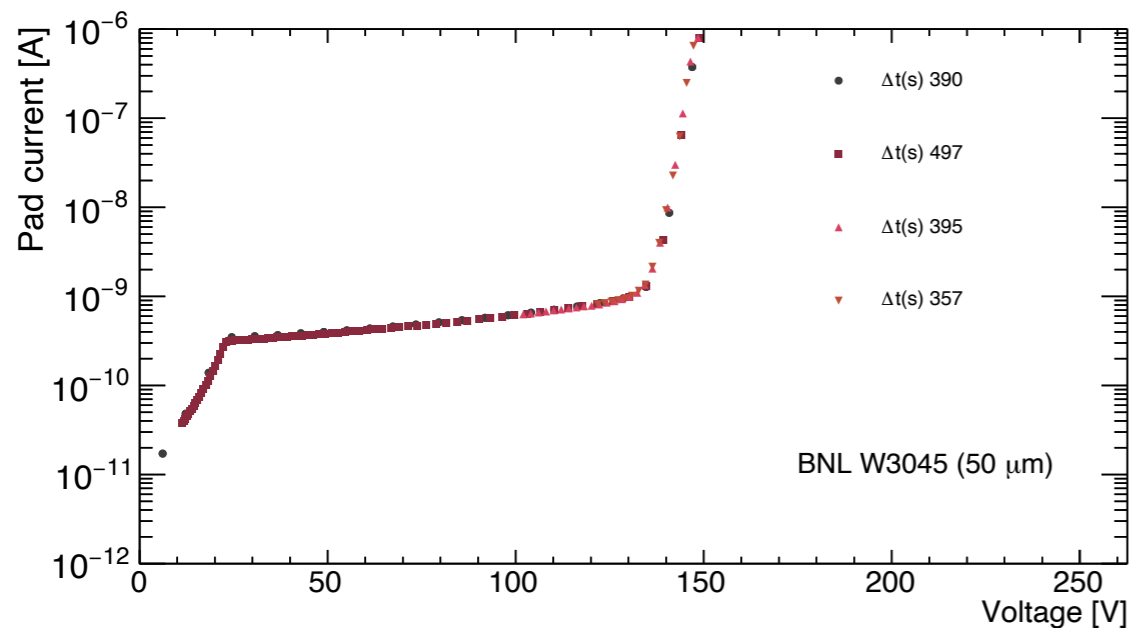


Leakage Current vs. Relative Humidity at 100.0 V



Conclusions

- Preliminary study on environmental conditions stress tests on (AC) LGADs
 - ▶ Prompted by investigation on applications of (AC) LGADs to space-based experiments.
 - ◆ Payload considerations, temperature control, current-draw limitations on satellites.
 - ▶ Ongoing systematic study on the impact of environmental operating conditions on physics performance.
 - ▶ Investigating mitigation strategies for environmental factors that degrade their performance
 - ▶ BNL-produced LGADs show good performance despite harsh operating conditions.
- Outlook:
 - ▶ Expand the phase space of environmental parameters.
 - ▶ Evaluation of long-term effects and prolonged operations under harsh conditions.
 - ▶ Confront results with ionization coefficients from TCAD models [1]
 - ▶ Analyze full effects on waveforms with TCT and test-beam setups.
- Lead to optimized sensor design for space-based applications.

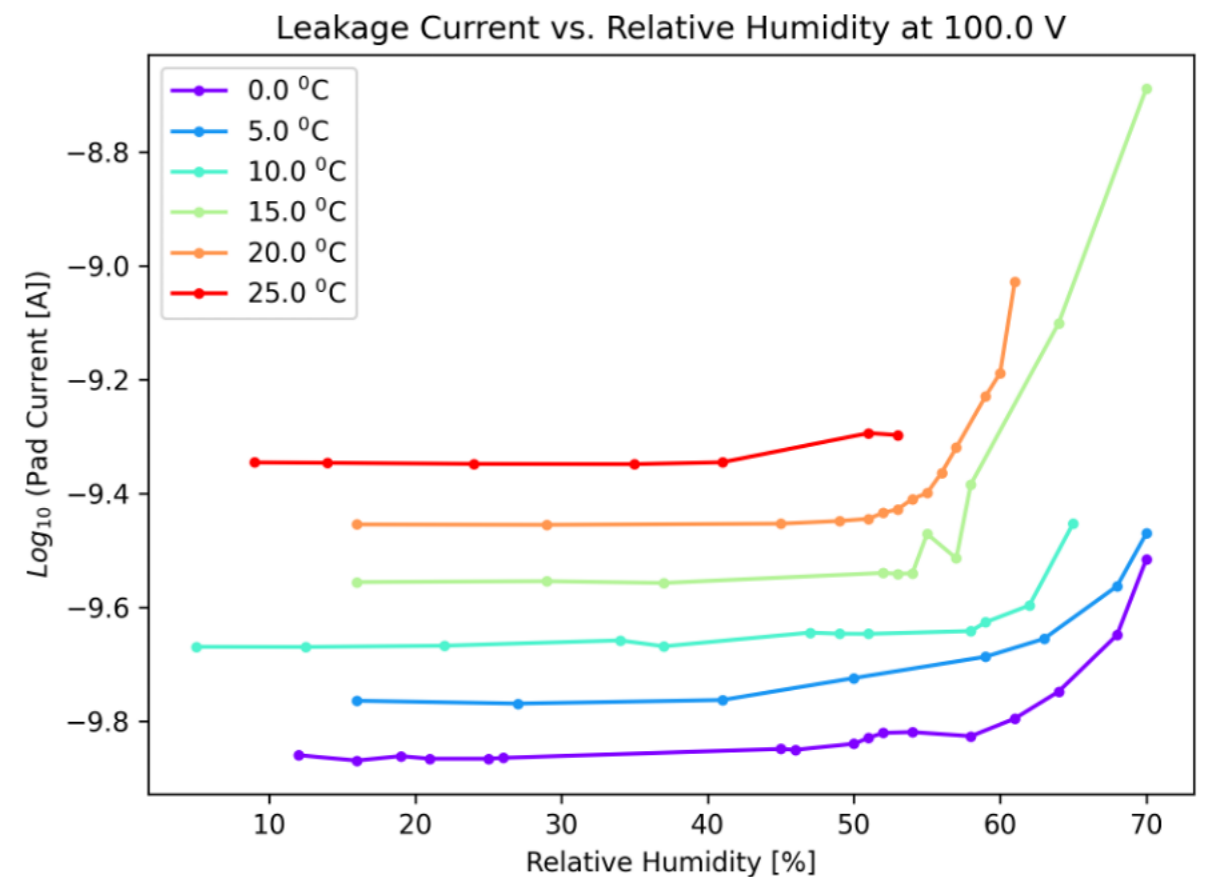
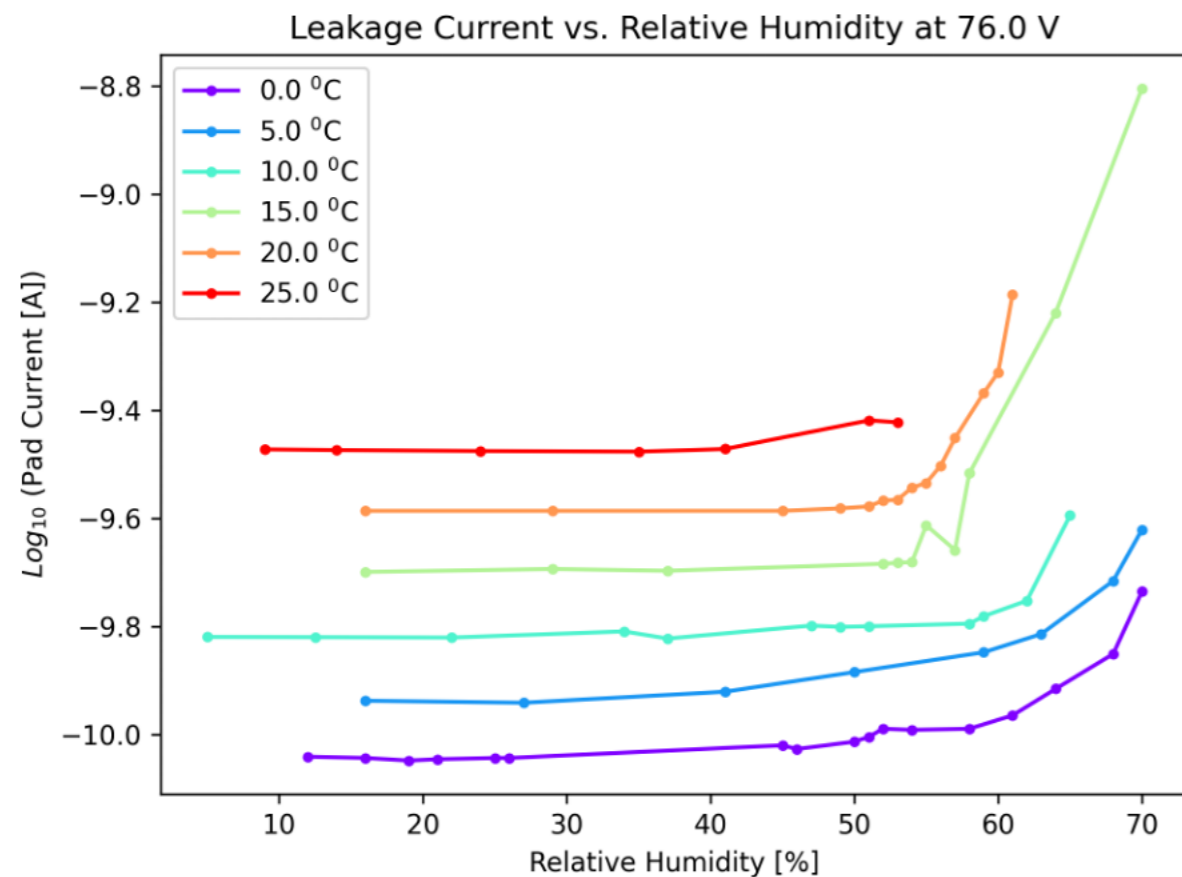


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Additional material.

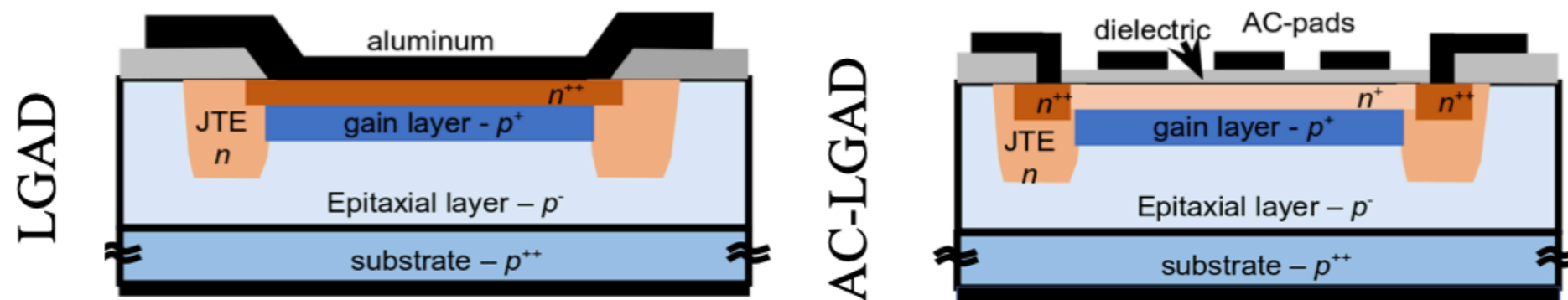
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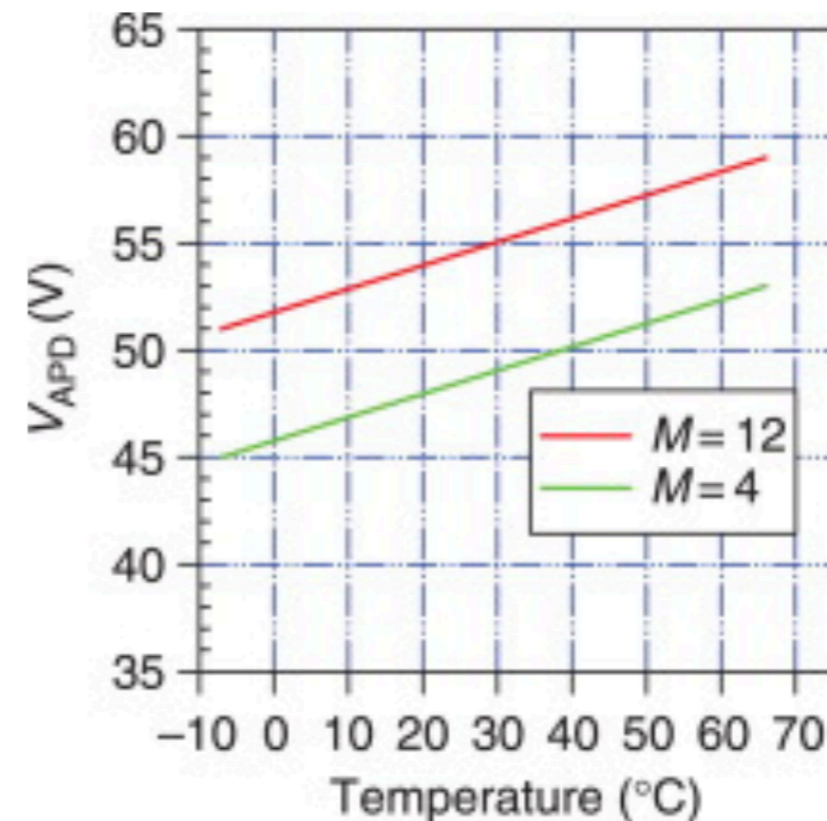
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 - ▶ Application starting to be investigated for space-based experiments [1]
- Large set of studies actively performed on Resistive Silicon Devices and specifically LGADs & AC-LGADs
 - Space applications require the study of LGAD behavior in a wide range of environmental conditions.
 - ▶ Temperature variations -100°C and $+100^\circ\text{C}$
 - ▶ Cryogenic/temperature control not ensured (payload)
 - Need to ensure good sensor response and electrical characteristics at varying operating conditions.
 - ▶ Leakage current is a function of T
 - ▶ Need easy-to-model
 - ▶ The behaviour of charge carriers in silicon strongly affected by T

Temperature mechanisms

- Avalanche as a function of temperature.
 - ▶ The ability of carriers to ionize depends on the bandgap and the band structure
 - ◆ In turn, they depend on the temperature.
 - ▶ Phonon scattering is affected by temperature.
 - ◆ At high temperatures carriers lose their energy when traveling through the multiplication region and require longer paths before they impact ionization.



M.M. Hayat, in *Comprehensive Semiconductor Science and Technology*, 2011